



# Powered-off Protection, 6 $\Omega$ , 1.8 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer)

### **DESCRIPTION**

The DG9411E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of 6  $\Omega$  and switch off capacitance of 7 pF at a 5 V power supply and low power consumption, and fast switching speeds.

The DG9411E can handle both analog and digital signals and permits signals with amplitudes of up to V+ to be transmitted in either direction. Its control logic inputs can go over V+ up to 5.5 V. It features break before make switching performance.

A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to V+ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).

Operation temperature is specified from -40  $^{\circ}$ C to +85  $^{\circ}$ C. The DG9411E is available in the compact SC-70-6L package.

## **FEATURES**

- Low switch on-resistance (6 Ω)
- 1.8 V to 5.5 V single supply operation
- Powered-off protection
- Control logic inputs can go over V+ up to 5.5 V
- · Low parasitic capacitance, 7 pF at switch off
- Low charge injection, 1 pC
- Break before make switching
- Latch-up performance exceeds 200 mA per JESD 78
- ESD tested
  - 7000 V human body model (JS-001)
  - 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

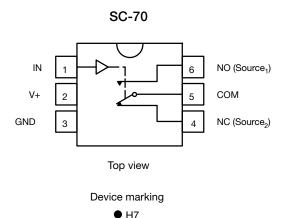
### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### **APPLICATIONS**

- Battery powered devices
- · Smartphones and tablets
- · Consumer and computing
- Portable instrumentation
- Medical equipment

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
LOGIC	NC	NO				
0	On	Off				
1	Off	On				

### Notes

- Logic "0" ≤ 0.8 V
- Logic "1" ≥ 2.4 V

ORDERING INFORMATION					
TEMP. RANGE	PACKAGE	PART NUMBER			
-40 °C to +85 °C	SC-70-6	DG9411EDL-T1-GE3			

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER		LIMIT	UNIT		
V+, COM, NC, NO, IN reference to GN	D	-0.3 to 6	V		
Continuous current (any terminal)		± 50	mA		
Peak current (pulsed at 1 ms, 10 % du	ty cycle)	± 200	IIIA		
Storage temperature		-65 to +150	°C		
Power dissipation (packages) <sup>a</sup>	6-pin SC-70 <sup>b</sup>	250	mW		
ESD / HBM JS-001		7000	V		
ESD / CDM	JS-002	1000	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
Latch up	Per JESD78 with 1.5 x voltage clamp	200	mA		

# Notes

- a. All leads welded or soldered to PC board b. Derate 3.1 mW/°C above 70 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

<b>SPECIFICATIONS</b> (V+	= 5 V)	TEST CONDITIONS			LIMITS		
PARAMETER	CVMDOL	LINI ESS OTHERWISE SPECIFIED	TEMP.a	-40 °C to +85 °C			UNIT
	STIVIBOL		I EIVIP.	MIN. b	TYP. °	MAX. b	UNII
Analog Switch							
Analog signal range d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
Drain-source on-resistance d	R	V+ = 4.5 V, V <sub>COM</sub> = 3 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	-	6	9	
Dialii-source on-resistance	R <sub>DS(on)</sub>	V+ = 4.5 V, VCOM = 5 V, INO, INC = 10 IIIA	Full	-	8	11	
R <sub>DS(on)</sub> flatness <sup>d</sup>	R <sub>DS(on)</sub> flatness	$V+ = 5 \text{ V}, V_{COM} = 1.5 \text{ V}, 3.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room	ı	0.4	-	Ω
R <sub>DS(on)</sub> match <sup>d</sup>	$\Delta R_{DS(on)}$	$V_{+} = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room	-	0.04	0.2	
	$I_{NO(off)}$ ,		Room	-1.5	-	1.5	
Switch-off leakage current f	I <sub>NC(off)</sub>	V+ = 5.5 V,	Full	-4	-	4	1
Switch-off leakage current	1	$V_{NO}$ , $V_{NC} = 1 \text{ V} / 4.5 \text{ V}$ , $V_{COM} = 4.5 \text{ V} / 1 \text{ V}$	Room	-1	-	1	- A
	I <sub>COM(off)</sub>		Full	-4	-	4	nA
Observation lead as a second f		V + = 5.5 V,	Room	-1	-	1	
Channel-on leakage current f	I <sub>COM(on)</sub>	$V_{NO}$ , $V_{NC} = V_{COM} = 1 \text{ V} / 4.5 \text{ V}$	Full	-4	-	4	
		$V+=0$ V, $V_{COM}=5$ V, NO/NC open, $V_{IN}=GND$	Full	-	-	2	
Power-down leakage	$I_{PD}$	V+ = 0 V, V <sub>NO</sub> , V <sub>NC</sub> = 5 V, COM open, V <sub>IN</sub> = GND	Full	-	-	2	μA
Digital Control					•	•	
Input high voltage	V <sub>INH</sub>		Full	2.4	-	-	V
Input low voltage	$V_{INL}$		Full	-	-	0.8	ľ
Input capacitance d	C <sub>IN</sub>		Full	-	6	-	рF
Input current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	t		Room	-	10	30	
Turri-ori tirrie -	t <sub>ON</sub>		Full	1	-	32	
Turn-off time d	+	$V_{NO}$ or $V_{NC} = 3 \text{ V}$ , $R_{L} = 300 \Omega$ , $C_{L} = 35 \text{ pF}$	Room	1	8	24	ns
Turn-on time	t <sub>OFF</sub>		Full	-	-	26	
Break-before-make time <sup>d</sup>	t <sub>BBM</sub>		Room	1	-	-	
Charge injection <sup>d</sup>	$Q_{INJ}$	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room		1	-	рС
Off-isolation <sup>d</sup>	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		-78	-	dB
Crosstalk d	X <sub>TALK</sub>	$n_L = 30 \Omega$ , $O_L = 3 \text{ pr}$ , $I = 1 \text{ M/H/2}$	Room	-	-77	-	ub
NO NO off conscitones d	C <sub>NO(off)</sub>	V <sub>IN</sub> = 0 V or V+, f = 1 MHz	Room	-	7	-	
NO, NC off capacitance d	C <sub>NC(off)</sub>		Room	-	7	-	pF
Channel-on capacitance d	C <sub>ON</sub>	<u>1</u>		-	13	-	
Power Supply							
Power supply current d	l+	$V_{IN} = 0 \text{ V or V} +$	Full	-	0.004	1	μΑ



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.a	<b>LIMITS</b> -40 °C to +85 °C			UNIT
	01202	$V+ = 3 V, \pm 10 \%$ $V_{IN} = 0.4 V \text{ or } 2 V^e$		MIN. b	TYP. c	MAX. b	_
Analog Switch							
Analog signal range <sup>d</sup>	$V_{NO}, V_{NC} V_{COM}$		Full	0	-	V+	>
Drain-source on-resistance d	B	V+ = 2.7 V, V <sub>COM</sub> = 1.5 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	ı	13	22	
Dialii-Source on-resistance	R <sub>DS(on)</sub>	V+ = 2.7 V, VCOM = 1.5 V, INO, INC = 10 IIIA	Full	-	15	24	
R <sub>DS(on)</sub> flatness <sup>d</sup>	R <sub>DS(on)</sub> flatness	$V+ = 3 V$ , $V_{COM} = 0 V$ to $V+$ , $I_{NO}$ , $I_{NC} = 10 \text{ mA}$	Room	-	1.4	-	Ω
R <sub>DS(on)</sub> match <sup>d</sup>	$\Delta R_{DS(on)}$	V+ = 2.7 V, V <sub>COM</sub> = 1.5 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	-	0.03	0.35	
	I <sub>NO(off)</sub> ,		Room	-400	-	400	рА
Switch-off leakage current f	I <sub>NC(off)</sub>	V+ = 3.3 V,	Full	-4	-	4	nA
Switch-on leakage current		$V_{NO}$ , $V_{NC} = 1 \text{ V} / 3 \text{ V}$ , $V_{COM} = 3 \text{ V} / 1 \text{ V}$	Room	-800	-	800	рА
	I <sub>COM(off)</sub>		Full	-8	-	8	nA
Channel on leakage ourrent f	ı	V+ = 3.3 V,	Room	-800	-	800	pА
Channel-on leakage current f	I <sub>COM(on)</sub>	$V_{NO}, V_{NC} = V_{COM} = 1 \text{ V} / 3 \text{ V}$	Full	-8	-	8	nA
Digital Control							
Input high voltage	$V_{INH}$		Full	2	-	-	V
Input low voltage	$V_{INL}$		Full	-	-	0.4	٧
Input capacitance d	C <sub>IN</sub>		Full	ı	6	-	рF
Input current	$I_{\text{INL}}$ or $I_{\text{INH}}$	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	+		Room	1	13	34	
rum-on time -	t <sub>ON</sub>		Full	-	-	37	
Turn-off time d	+	$V_{NO}$ or $V_{NC}$ = 2 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room	-	9	20	ns
rum-on time «	t <sub>OFF</sub>		Full	-	-	22	
Break-before-make time <sup>d</sup>	t <sub>BBM</sub>		Room	1	-	-	
Charge injection <sup>d</sup>	$Q_{INJ}$	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	0.9	-	рС
Off-isolation d	OIRR	D - 50 0 C - 5 x 5 f - 1 MHz	Room	-	-78	-	dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-	-77	-	uв
NO NC off conseitance d	C <sub>NO(off)</sub>	$V_{IN} = 0 \text{ V or V+, f} = 1 \text{ MHz}$	Room	-	7	-	pF
NO, NC off capacitance d	C <sub>NC(off)</sub>		Room	-	7	-	
Channel-on capacitance d	C <sub>ON</sub>		Room	-	14	-	
Power Supply							
Power supply current <sup>d</sup>	l+	V <sub>IN</sub> = 0 V or V+	Full	-	0.002	1	μΑ



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PARAMETER	SYMBOL TEST CONDITIONS UNLESS OTHERWISE SPECIFIED $V+=2.5\ V,\pm\ 10\ \%$ $V_{IN}=0.4\ V\ or\ 2\ V\ e$		TEMP.a	<b>LIMITS</b> -40 °C to +85 °C			UNIT
			MIN. b	TYP. c	MAX. b		
Analog Switch							
Analog signal range <sup>d</sup>	$V_{NO}, V_{NC} V_{COM}$		Full	0	-	V+	>
Drain-source on-resistance d	R <sub>DS(on)</sub>	V+ = 2.2 V, V <sub>COM</sub> = 1 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	-	23	29.5	
R <sub>DS(on)</sub> flatness <sup>d</sup>	R <sub>DS(on)</sub>	V+ = 2.5 V, V <sub>COM</sub> = 0 V to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Full <sup>d</sup> Room	-	1.7	30.5	Ω
R <sub>DS(on)</sub> match <sup>d</sup>	$\Delta R_{DS(on)}$	V+ = 2.2 V, V <sub>COM</sub> = 1.2 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	-	0.1	0.5	
20(01)	I <sub>NO(off)</sub> ,	7 NO. NO.	Room	-200	-	200	рА
0 " 1 " 1 1 1 1 1 1 1 1	I <sub>NC(off)</sub>	V+ = 2.7 V	Full <sup>d</sup>	-3	-	3	nA
Switch-off leakage current f		$V_{NO}$ , $V_{NC} = 0.5 \text{ V} / 1.5 \text{ V}$ , $V_{COM} = 1.5 \text{ V} / 0.5 \text{ V}$	Room	-200		200	рА
	I <sub>COM(off)</sub>	Full d	-3	-	3	nA	
Observation to the town of the		V+ = 2.7 V,	Room	-200	-	200	рА
Channel-on leakage current f	$V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	$V_{NO}$ , $V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Full <sup>d</sup>	-3	-	3	nA
Digital Control							
Input high voltage	V <sub>INH</sub>		Full	2	-	-	V
Input low voltage	$V_{INL}$		Full	-	-	0.4	V
Input capacitance d	C <sub>IN</sub>		Full	-	6	-	pF
Input current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	t <sub>ON</sub>		Room	-	16	36	l
Turn on time	UN		Full <sup>d</sup>	-	-	38	Į
Turn-off time d	t <sub>OFF</sub>	$V_{NO}$ or $V_{NC}$ = 1.5 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room	-	10	19	ns
Turr on time	UFF		Full	-		21	Į
Break-before-make time <sup>d</sup>	t <sub>BBM</sub>		Room d	1	-	-	
Charge injection <sup>d</sup>	Q <sub>INJ</sub>	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	0.9	-	рС
Off-isolation <sup>d</sup>	OIRR	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-	-78	-	dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	11 50 32, OL - 5 pr , r - 1 1911 12	Room	-	-77	-	UD.
NO, NC off capacitance d	C <sub>NO(off)</sub>		Room	-	7	-	
140, 140 on capacitance	C <sub>NC(off)</sub>	$V_{IN} = 0 \text{ V or V+, f} = 1 \text{ MHz}$	Room	-	7	-	pF
Channel-on capacitance d	C <sub>ON</sub>	1		-	14	-	
Power Supply							
Power supply current d	I+	$V_{IN} = 0 \text{ V or V} +$	Full	-	-	1	μA



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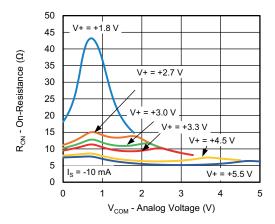
SPECIFICATIONS (V+ = 2 V)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.a	<b>LIMITS</b> -40 °C to +85 °C			UNIT
		$V+ = 2 V, \pm 10 \%$ $V_{IN} = 0.4 V \text{ or } 1.6 V ^{e}$		MIN. b	TYP. c	MAX. b	
Analog Switch							
Analog signal range <sup>d</sup>	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
Drain-source on-resistance d	R <sub>DS(on)</sub>	V+ = 1.8 V, V <sub>COM</sub> = 1 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room Full <sup>d</sup>	-	37 36	45 47	
R <sub>DS(on)</sub> flatness <sup>d</sup>	R <sub>DS(on)</sub> flatness	V+ = 2 V, V <sub>COM</sub> = 0 V to V+, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	-	3	-	Ω
R <sub>DS(on)</sub> match <sup>d</sup>	$\Delta R_{DS(on)}$	V+ = 1.8 V, V <sub>COM</sub> = 1 V, I <sub>NO</sub> , I <sub>NC</sub> = 10 mA	Room	-	0.04	0.5	
, ,	I <sub>NO(off)</sub> ,		Room	-200	-	200	рΑ
Curitab off looks as surrent f	I <sub>NC(off)</sub>	V+ = 2.2 V,	Full <sup>d</sup>	-3	-	3	nA
Switch-off leakage current f		$V_{NO}$ , $V_{NC} = 0.5 \text{ V} / 1.5 \text{ V}$ , $V_{COM} = 1.5 \text{ V} / 0.5 \text{ V}$	Room	-200	-	200	рΑ
	I <sub>COM(off)</sub>		Full <sup>d</sup>	-3	-	3	nA
		V+ = 2.2 V,	Room	-200	-	200	рΑ
Channel-on leakage current f	ICOM(on)	$V_{NO}$ , $V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Full <sup>d</sup>	-3	-	3	nA
Digital Control							
Input high voltage	V <sub>INH</sub>		Full	1.6	-	-	V
Input low voltage	$V_{INL}$		Full	-	-	0.4	v
Input capacitance d	C <sub>IN</sub>		Full	-	6	-	pF
Input current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μA
Dynamic Characteristics							
Turn-on time d	tou		Room	-	21	40	
rum-on time	t <sub>ON</sub>		Full <sup>d</sup>	-	-	42	
Turn-off time d	toff	$V_{NO}$ or $V_{NC}$ = 1.5 V, $R_L$ = 300 $\Omega$ , $C_L$ = 35 pF	Room	-	13	20	ns
rum-on time	UFF		Full <sup>d</sup>	-	-	21	
Break-before-make time <sup>d</sup>	t <sub>BBM</sub>		Room	1	-	-	
Charge injection <sup>d</sup>	$Q_{INJ}$	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	0.8	-	рC
Off-isolation d	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room	-	-78	-	dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	11 = 30 32, Ο[ = 3 μι , ι = ι ινιπε	Room	-	-77	-	ub
NO, NC off capacitance d	C <sub>NO(off)</sub>		Room	-	7	-	
ivo, ivo on capacitance	C <sub>NC(off)</sub>	$V_{IN} = 0 \text{ V or V+, f} = 1 \text{ MHz}$	Room	-	7	-	pF
Channel-on capacitance d	C <sub>ON</sub>		Room	-	14	-	
Power Supply							
Power supply current <sup>d</sup>	l+	$V_{IN} = 0 \text{ V or V} +$	Full	-	-	1	μA

### Notes

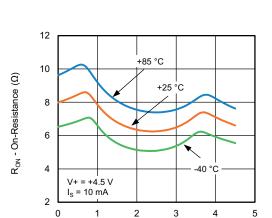
- a. Room = 25 °C, full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, nor subjected to production test
- e.  $V_{IN}$  = input voltage to perform proper function
- f. Guaranteed by 5 V leakage testing, not production tested



# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

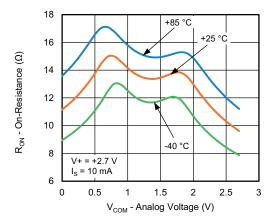


R<sub>DS(on)</sub> vs. V<sub>COM</sub> and Supply Voltage

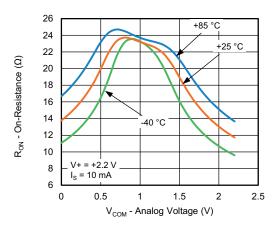


R<sub>DS(on)</sub> vs. Analog Voltage and Temperature

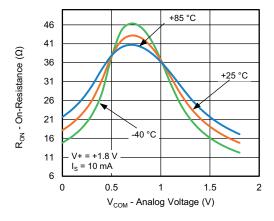
V<sub>COM</sub> - Analog Voltage (V)



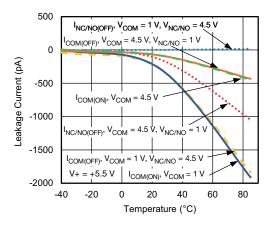
R<sub>DS(on)</sub> vs. Analog Voltage and Temperature



R<sub>DS(on)</sub> vs. Analog Voltage and Temperature



R<sub>DS(on)</sub> vs. Analog Voltage and Temperature

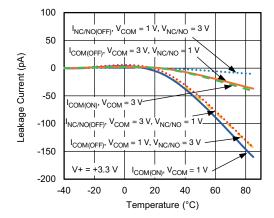


Leakage Current vs. Temperature

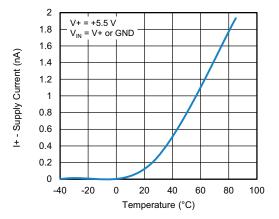
For technical questions, contact: analogswitchte



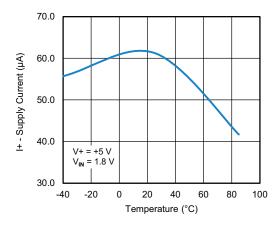
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



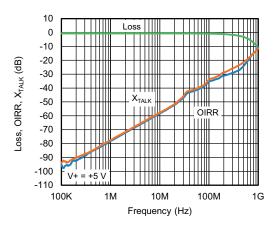
Leakage Current vs. Temperature



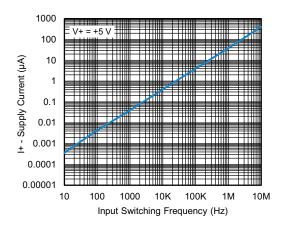
Supply Current vs. Temperature



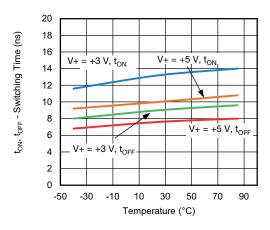
Supply Current vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency



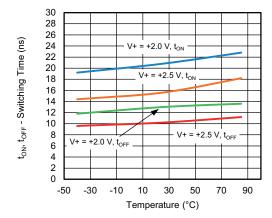
**Supply Current vs. Input Switching Frequency** 



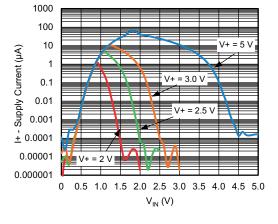
Switching Time vs. Temperature



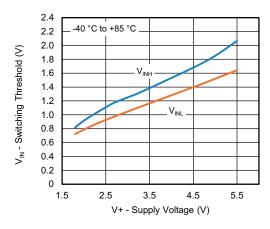
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



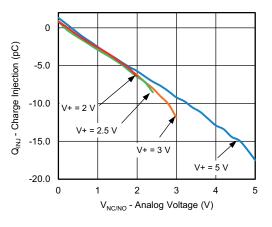
Switching Time vs. Temperature



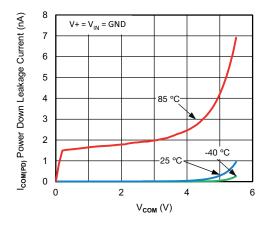
Supply Current vs. Enable Input Voltage



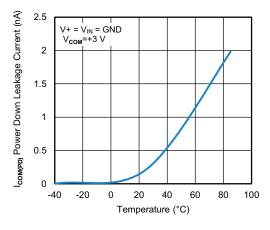
Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage



Power Down Leakage Current vs V<sub>COM</sub>

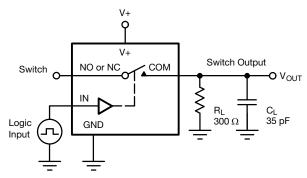


Power Down Leakage Current vs Temperature

For technical questions, contact: analogswitchte

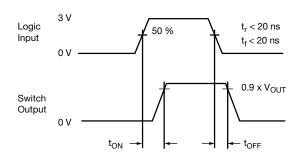


# **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = switch on

Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

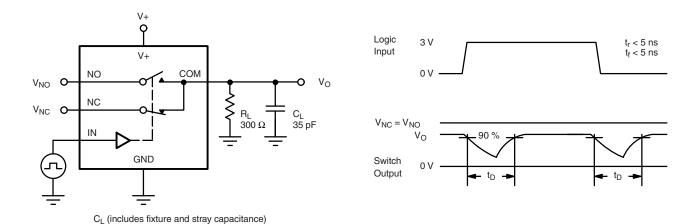


Fig. 2 - Break-Before-Make Interval

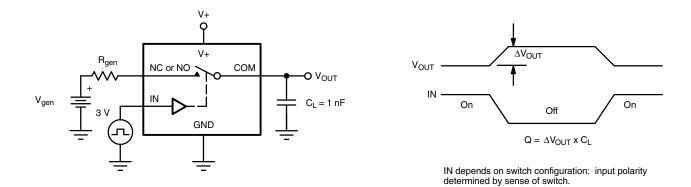


Fig. 3 - Charge Injection

Analyzer

**TEST CIRCUITS** 

# Off Isolation = 20 log $\frac{V_{NC/NO}}{V_{COM}}$

Fig. 4 - Off-Isolation

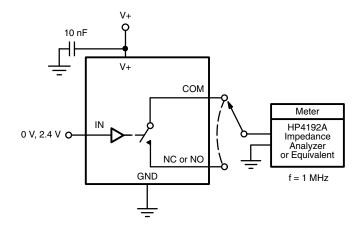


Fig. 5 - Channel Off / On Capacitance



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# Vishay Siliconix

PRODUCT SUMMARY	
Part number	DG9411E
Status code	2
Configuration	SPDT x 1
Single supply min. (V)	1.8
Single supply max. (V)	5.5
Dual supply min. (V)	-
Dual supply max. (V)	-
On-resistance (Ω)	6
Charge injection (pC)	1
Source on capacitance (pF)	13
Source off capacitance (pF)	7
Leakage switch on typ. (nA)	-
Leakage switch off max. (nA)	1.5
-3 dB bandwidth (MHz)	-
Package	SC-70-6
Functional circuit / applications	Multi Purpose, instrumentation, medical and healthcare, portable
Interface	Parallel
Single supply operation	Yes
Dual supply operation	-
Turn on time max. (ns)	30
Crosstalk and off isolation	-77

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?76294">www.vishay.com/ppg?76294</a>.



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